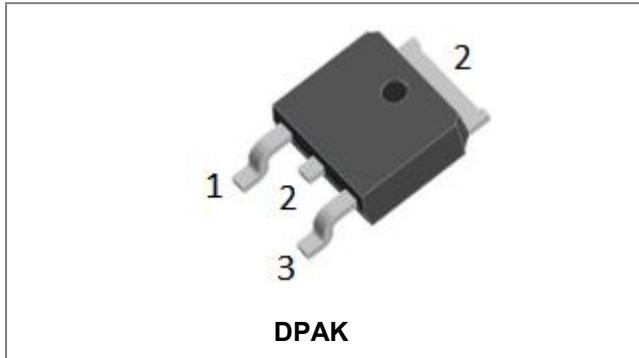


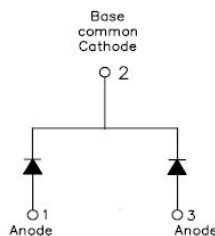
## SDURD620CT ULTRAFAST RECTIFIER



### Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

### Circuit Diagram



### Features

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- This is a Pb – free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	-	200	V
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_c=90^\circ\text{C}$ , rectangular wave form	3(Per Leg) 6(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	$I_{FSM}$	8.3ms, Half Sine pulse	80	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (Per Leg)*	$V_{F1}$	@ 3A, Pulse, $T_J = 25^\circ\text{C}$	1.05	1.20	V
	$V_{F2}$	@ 3A, Pulse, $T_J = 125^\circ\text{C}$	0.87	1.00	V
Reverse Current (Per Leg)*	$I_{R1}$	@ $V_R = \text{rated } V_R, T_J = 25^\circ\text{C}$	0.03	5	$\mu\text{A}$
	$I_{R2}$	@ $V_R = \text{rated } V_R, T_J = 125^\circ\text{C}$	5	500	$\mu\text{A}$
Reverse Recovery Time (Per Leg)	$t_{rr}$	$I_F=500\text{mA}, I_R=1\text{A}, \text{and } I_m=250\text{mA}$	31	35	ns

\* Pulse width < 300  $\mu\text{s}$ , duty cycle < 2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	$T_{\text{stg}}$	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	DC operation	4.5	$^{\circ}\text{C}/\text{W}$
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

**Ratings and Characteristics Curves**

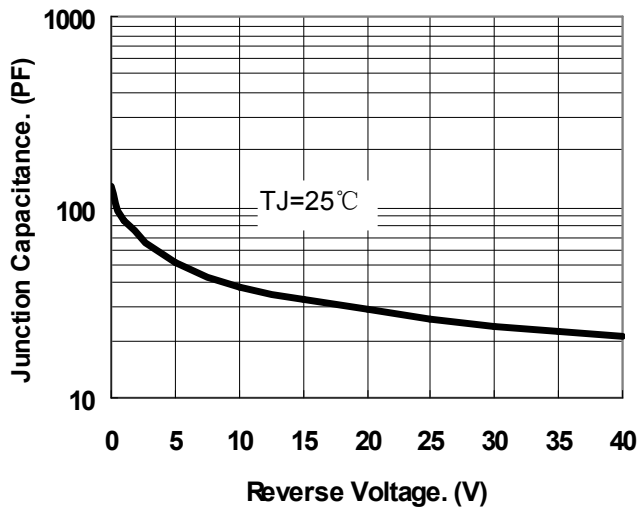


Fig.1-Typical Junction Capacitance

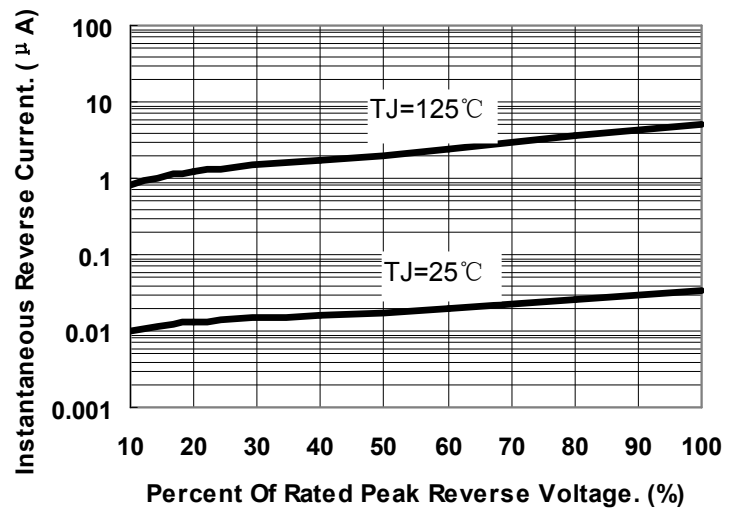


Fig.2-Typical Reverse Characteristics

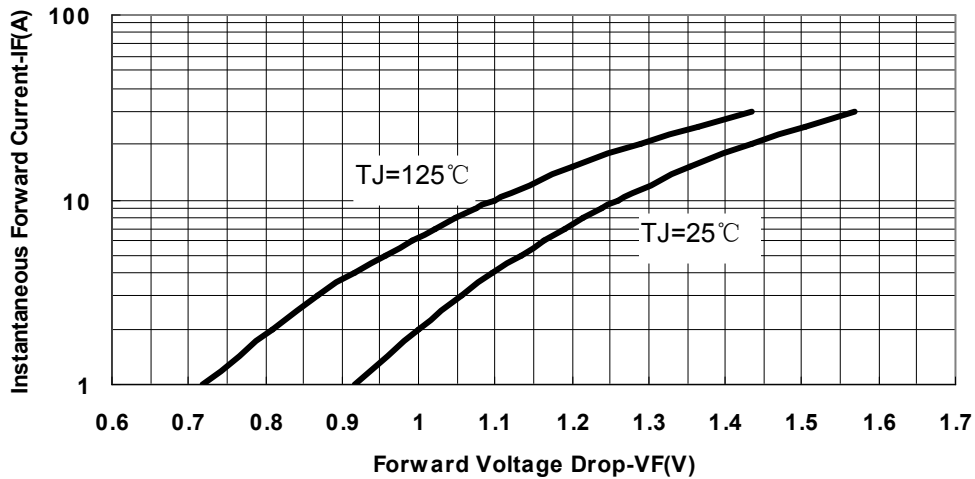
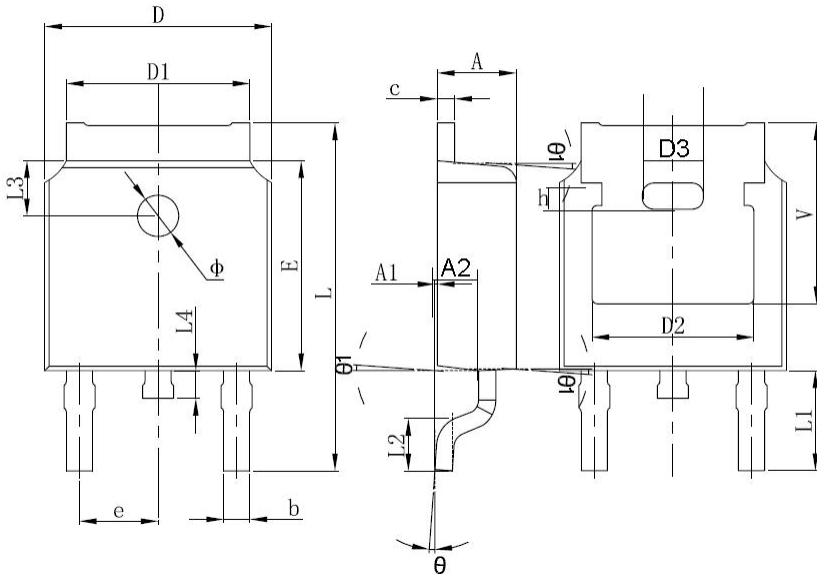


Fig.3-Typical Instantaneous Forward Voltage Characteristics

**Mechanical Dimensions DPAK**



SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.40	0.087	0.094
A1	0.00	0.127	0.000	0.005
b	0.66	0.86	0.026	0.034
c	0.46	0.60	0.018	0.024
D	6.50	6.70	0.256	0.264
D1	5.13	5.46	0.202	0.215
D2	4.83 REF.		0.190 REF.	
E	6.00	6.20	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.70	10.40	0.381	0.409
L1	2.90 REF.		0.144 REF.	
L2	1.40	1.70	0.055	0.067
L3	1.60 REF.		0.063 REF.	
L4	0.60	1.00	0.024	0.039
Φ	1.10	1.30	0.043	0.051
Θ	0°	8°	0°	8°
h	0.00	0.30	0.000	0.012
V	5.35 REF.		0.211 REF.	

**Ordering Information**

Device	Package	Shipping
SDURD620CT	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel Packaging specification.

**Marking Diagram**

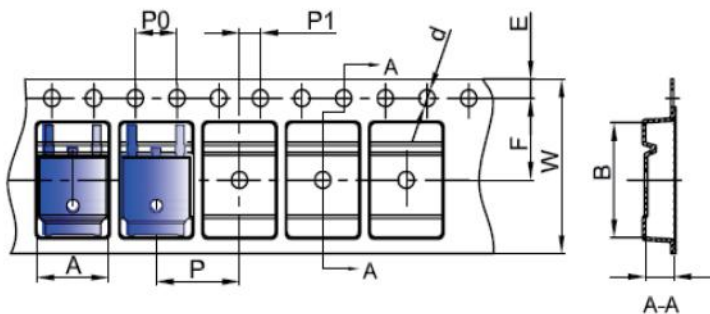


Where XXXXX is YYWWL

- SDUR = Device Type
- D = Package type
- 6 = Forward Current (6A)
- 20 = Reverse Voltage (200V)
- CT = Configuration
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Carrier Tape Specification DPAK**



SYMBOL	Millimeters	
	Min.	Max.
A	6.80	7.00
B	10.40	10.60
C	2.60	2.80
d	Φ1.45	Φ1.65
E	1.65	1.85
F	7.40	7.60
P0	3.90	4.10
P	7.90	8.10
P1	1.90	2.10
W	15.90	16.30

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